

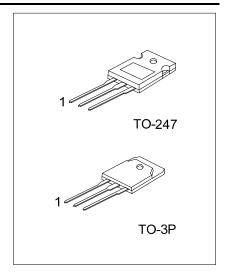
20N60 Power MOSFET

20A, 600V N-CHANNEL POWER MOSFET

DESCRIPTION

The UTC **20N60** is an N-channel enhancement mode power MOSFET using UTC's advanced technology to provide customers with planar stripe and DMOS technology. This technology is specialized in allowing a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

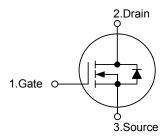
The UTC **20N60** is universally applied in motor control, UPS, DC choppers and switch-mode and resonant-mode power supplies.



■ FEATURES

- * $R_{DS(ON)} = 0.45\Omega @V_{GS} = 10V$
- * High switching speed

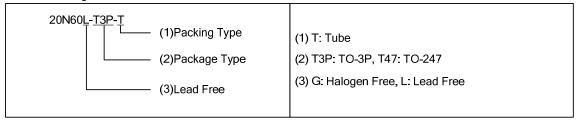
■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Daalaaaa	Pin Assignment			Daaldaa	
Lead Free	Halogen Free	Package	1	2	3	Packing	
20N60L-T3P-T	20N60G-T3P-T	TO-3P	G	D	S	Tube	
20N60L-T47-T	20N60G-T47-T	TO-247	G	D	S	Tube	

Note: Pin Assignment: G: Gate D: Drain S: Source



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■ ABSOLUTE MAXIMUM RATINGS (T_C =25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		V_{DSS}	600	V	
Gate-Source Voltage		V _{GSS}	±20	V	
Drain Current	Continuous	I _D	20	Α	
	Pulsed	I _{DM}	80	Α	
Avalanche Energy	Single Pulsed(Note 2)	E _{AS}	1200	mJ	
Power Dissipation	TO-3P		300	W	
	TO-247	P _D	370		
Junction Temperature		TJ	+150	°C	
Storage Temperature		T _{STG}	-55~+150	°C	

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT	
lunction to Cons	TO-3P	0	0.42	°C/\\	
Junction to Case	TO-247	AlC	0.34	°C/W	

■ ELECTRICAL CHARACTERISTICS (Ty=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT		
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =250μA, V _{GS} =0V				V		
Drain-Source Leakage Current	I _{DSS}	V _{DS} =600V, V _{GS} =0V			10	μA		
Forward		V _{GS} =+20V, V _{DS} =0V			+100	nA		
Gate- Source Leakage Current Reverse	I_{GSS}	V _{GS} =-20V, V _{DS} =0V			-100	nA		
ON CHARACTERISTICS								
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS} = V_{GS} , I_D =250 μ A			4.0	V		
Static Drain-Source On-State Resistance		V _{GS} =10V, I _D =10A, Pulse test, t≤300µs, duty cycle d≤2%		0.22	0.45			
Static Drain-Source On-State Resistance	$R_{DS(ON)}$			0.32	0.45	Ω		
DYNAMIC PARAMETERS								
Input Capacitance	C _{ISS}			4500		pF		
Output Capacitance	Coss	V _{GS} =0V, V _{DS} =25V, f=1MHz		420		pF		
Reverse Transfer Capacitance	C_{RSS}			140		pF		
SWITCHING PARAMETERS								
Total Gate Charge	Q_{G}	V _{GS} =10V, V _{DS} =300V, I _D =10A (Note 1, 2)		150	170	nC		
Gate to Source Charge	Q_{GS}			29	40	nC		
Gate to Drain Charge	Q_{GD}			60	85	nC		
Turn-ON Delay Time	t _{D(ON)}			20	40	ns		
Rise Time	t _R	V_{GS} =10V, V_{DS} =300V, I_{D} =10A, R_{G} =2 Ω ,		43	60	ns		
Turn-OFF Delay Time	t _{D(OFF)}	(Note 1, 2)		70	90	ns		
Fall-Time	t _F			40	60	ns		
SOURCE- DRAIN DIODE RATINGS AND	CHARACT	ERISTICS						
Maximum Body-Diode Continuous	Is	V _{GS} =0V			20	^		
Current					20	Α		
Maximum Body-Diode Pulsed Current	I _{SM}	Repetitive			80	Α		
Drain-Source Diode Forward Voltage	V_{SD}	I _F =I _S , V _{GS} =0V, Pulse test, t≤300µs, duty cycle d≤2%			1.5	٧		
Body Diode Reverse Recovery Time	t _{rr}	$I_F = I_S, V_R = 100V, -di/dt = 100A/\mu s(Note 1)$		600		ns		

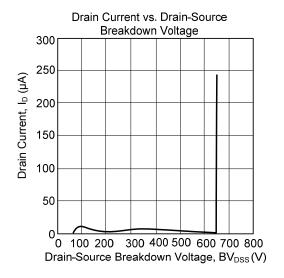
Notes: 1. Pulse Test: Pulse width ≤ 300µs, Duty cycle≤2%

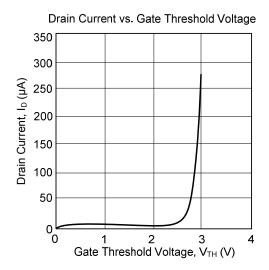
^{2.} V_{DD}=50V, Starting T_J=25°C, Peak I_{AS}=20A, L=6mH

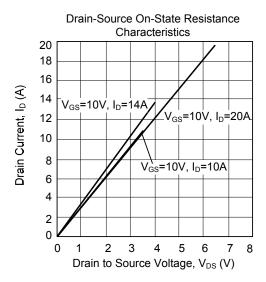
^{2.} Essentially independent of operating temperature

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■ TYPICAL CHARACTERISTICS







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